



ELECTRONICS INDUSTRY (USA) CO., LTD.

103 MOO 4, LATKRABANG EXPORT PROCESSING ZONE, LATKRABANG, BANGKOK 10520, THAILAND
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捷多邦, 专业PCB打样工厂, 24小时加急出货



Certificate Number: Q10561



Certificate Number: E17276

BR5000W - BR5010W

PRV : 50 - 1000 Volts
Io : 50 Amperes

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * High case dielectric strength

MECHANICAL DATA :

- * Case : Molded plastic with heatsink integrally mounted in the bridge encapsulation
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface for maximum heat transfer efficiency
- * Weight : 15.95 grams

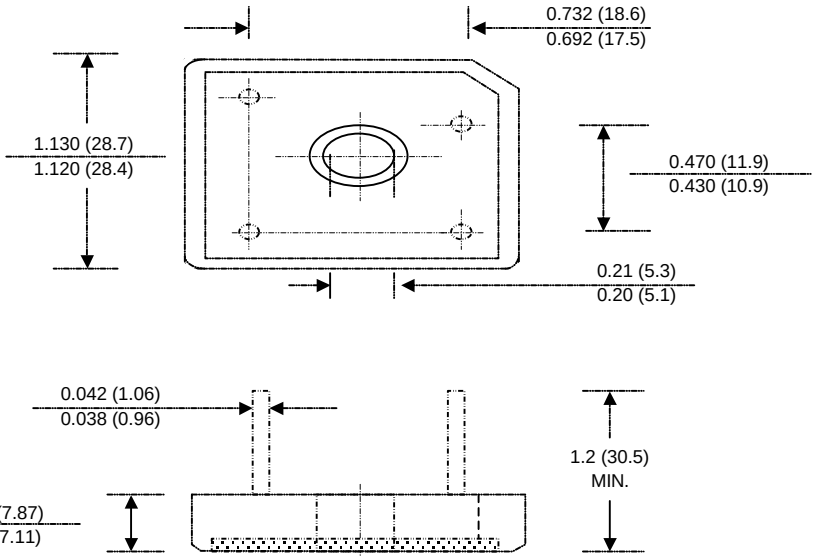
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	BR 5000W	BR 5001W	BR 5002W	BR 5004W	BR 5006W	BR 5008W	BR 5010W	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Current Tc=55°C	IF(AV)	50							Amps.
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	IFSM	400							Amps.
Current Squared Time at t < 8.3 ms.	I²t	664							A²S
Maximum Forward Voltage per Diode at If = 25 Amps.	VF	1.1							Volts
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta = 100 °C	IR	10							µA
	IR(H)	200							µA
Typical Thermal Resistance at Junction to Case (Note 1)	RθJC	1.0							°C/W
Operating Junction Temperature Range	TJ	- 40 to + 150							°C
Storage Temperature Range	TSTG	- 40 to + 150							°C

SILICON BRIDGE RECTIFIERS

BR50W



Dimensions in inches and (millimeters)



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RATING AND CHARACTERISTIC CURVES (BR5000W - BR5010W)

FIG.1 - DERATING CURVE FOR OUTPUT
RECTIFIED CURRENT

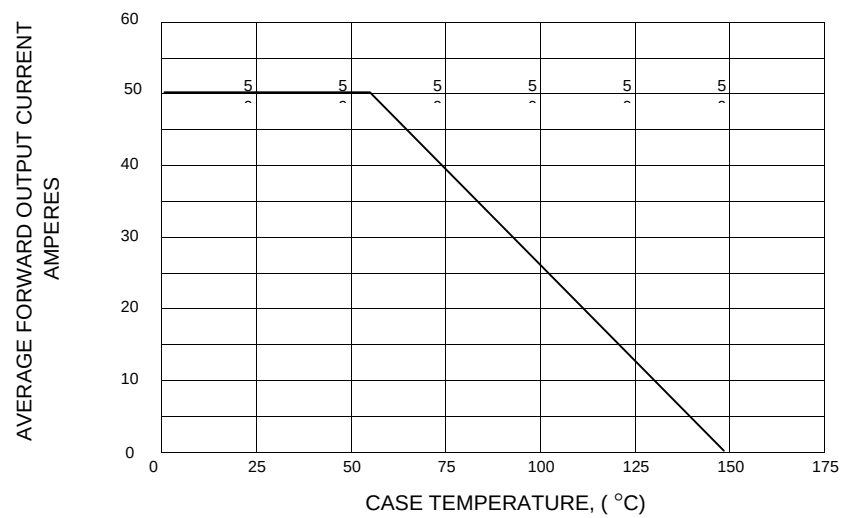


FIG.2 - MAXIMUM NON-REPETITIVE PEAK
FORWARD SURGE CURRENT

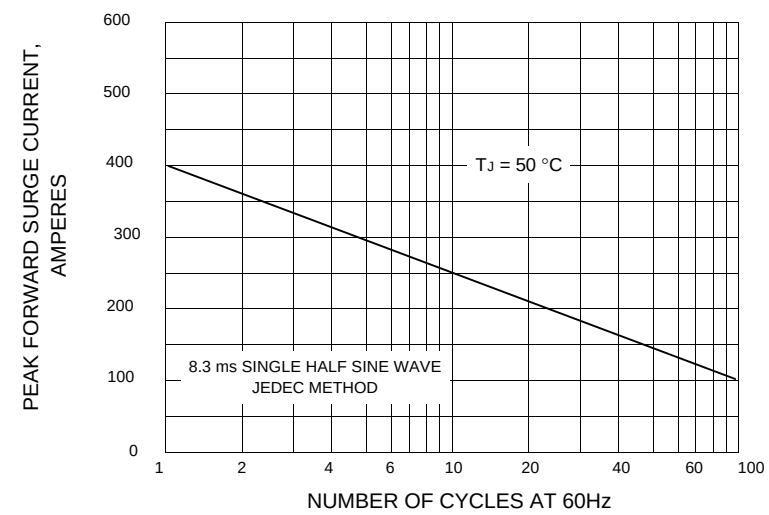


FIG.3 - TYPICAL FORWARD CHARACTERISTICS
PER DIODE

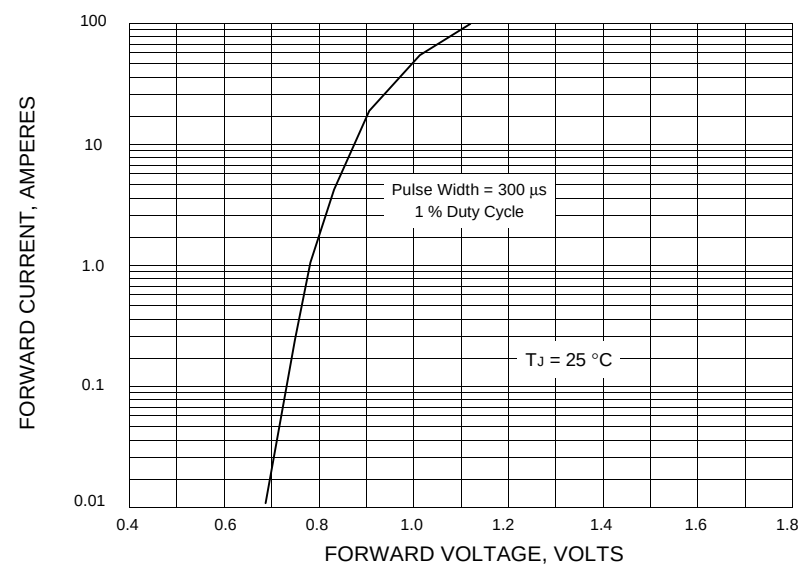
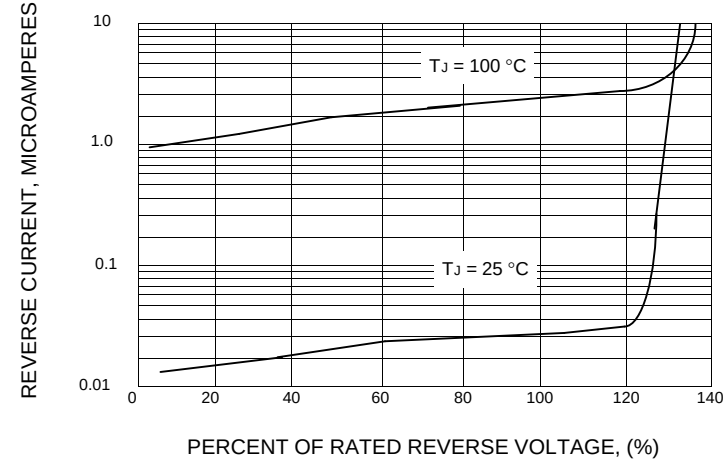


FIG.4 - TYPICAL REVERSE CHARACTERISTICS
PER DIODE



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